

CLAIMS

1. (original) An apparatus comprising:  
a thinned active semiconductor substrate;  
a support substrate for supporting the thinned active semiconductor substrate; and  
a magnetically permeable glue disposed between the active semiconductor substrate and  
the support substrate.
2. (original) The apparatus of claim 1 wherein the support substrate is magnetically permeable.
3. (original) The apparatus of claim 2 wherein the support substrate and the glue each comprise a magnetically permeable substance, the magnetically permeable substance comprising at least one of the group consisting of cobalt; nickel and iron.
4. (original) The apparatus of claim 3 wherein the support substrate comprises:  
a first layer having a coefficient of thermal expansion substantially equal to the integrated circuit, the first layer being in contact with the glue; and  
a second layer coupled to the first layer, the second layer comprising the magnetically permeable substance.
5. (original) The apparatus of claim 3 wherein the active semiconductor substrate comprises a magnetoresistive random access memory.
6. (original) The apparatus of claim 1 wherein the glue comprises:  
a bonding agent; and  
a magnetic permeability enhancing agent.
7. (original) The apparatus of claim 6 wherein the bonding agent comprises one of the group consisting of benzocyclobutene (BCB) and an epoxy.

8. (original) The apparatus of claim 6 wherein the magnetically permeable enhancing agent comprises at least one of the group consisting of cobalt, nickel and iron.

9. (original) The apparatus of claim 6 wherein the magnetic permeability enhancing agent comprises a plurality of magnetically-permeable, colloidal-sized particles suspended in the bonding agent.

10. (original) The apparatus of claim 9 wherein the glue has a first thickness and the particles have an average maximum dimension not substantially greater than half the first thickness.

11. (original) The apparatus of claim 9 wherein the active semiconductor substrate has a thickness of less than 200 microns.

12. (currently amended) An apparatus comprising:

a thinned integrated circuit wafer;

a support wafer having a first characteristic, ~~the first characteristic being at least one of the group consisting of thermally conductive, electrically conductive and being magnetically permeable~~ and comprising at least one of the group consisting of cobalt, nickel, and iron; and

a glue being magnetically permeable ~~having the first characteristic~~, the glue being disposed between the integrated circuit wafer and the support wafer and comprising at least one of the group consisting of cobalt, nickel, and iron.

13. (original) The apparatus of claim 12 wherein the integrated circuit wafer comprises a plurality of the integrated circuits.

14. (original) The apparatus of claim 13 wherein the apparatus comprises a three-dimensional wafer-to-wafer bonded structure including the integrated circuits, the substrate and the glue.

15. (currently amended) The apparatus of claim 12 wherein the glue comprises:

a bonding agent; and

~~a first characteristic~~ an enhancing agent that enhances magnetic permeability.

16. (original) The apparatus of claim 15 wherein the bonding agent comprises one of the group consisting of benzocyclobutene (BCB) and an epoxy.

17. (currently amended) ~~The~~ An apparatus of ~~claim 15~~ comprising:

a thinned integrated circuit wafer;

a support wafer having a first characteristic, the first characteristic being at least one of the group consisting of thermally conductive, electrically conductive and magnetically permeable; and

a glue having the first characteristic, the glue being disposed between the integrated circuit wafer and the support wafer;

wherein the glue comprises:

a bonding agent; and

a first characteristic enhancing agent;

wherein the first characteristic enhancing agent comprises a plurality of colloidal-sized particles suspended in the bonding agent, the colloidal particles being monolithic and coated nanosilica spheres.

18. (original) The apparatus of claim 12 wherein the glue has a first thickness and the particles have an average maximum dimension not substantially greater than half the first thickness.

19. (canceled)

20. (currently amended) The apparatus of claim ~~19~~ 12 wherein the ~~substrate support wafer~~ comprises:

~~a first layer having a coefficient of thermal expansion substantially equal to the integrated circuit, the first layer having the first surface; and~~  
a second layer comprising the magnetically permeable substance.

21. (currently amended) The apparatus of claim ~~19~~ 12 wherein the integrated circuit is a magnetic memory.

22. (original) The apparatus of claim 12 wherein the substrate comprises one of the group consisting of silicon carbide and heavily doped silicon.

23. (currently amended) ~~The~~ An apparatus of claim ~~12~~, wherein the first characteristic is comprising:

a thinned integrated circuit wafer;

a support wafer being electrically conductive, and the substrate and the glue each

comprise comprising at least one of the group consisting of metal and carbon; and

a glue being electrically conductive, the glue being disposed between the integrated circuit wafer and the support wafer and comprising at least one of the group consisting of metal and carbon.

24. (currently amended) The An apparatus of claim 12, wherein the first characteristic is comprising:

a thinned integrated circuit wafer;

a support wafer being thermally conductive, and the substrate and the glue each comprise comprising at least one of the group consisting of a metal, metal oxide, and cobalt; and

a glue being electrically conductive, the glue being disposed between the integrated circuit wafer and the support wafer and comprising at least one of the group consisting of a metal, metal oxide, and cobalt.

23. (withdrawn) A method of making a semiconductor device comprising:  
providing an integrated circuit bearing structure with a first surface;  
selecting a substrate structure material having a first characteristic, the first characteristic being at least one of the group consisting of thermally conductive, electrically conductive and magnetically permeable;  
providing a substrate structure comprised of the selected substrate structure material, the substrate structure having a second surface;  
providing a glue having the first characteristic; and  
gluing the integrated circuit bearing structure to the substrate structure using the glue.

24. (withdrawn) The method of claim 23 wherein the step of providing the glue comprises:

providing a bonding agent; and  
providing an amount of first characteristic enhancing agent; and  
mixing the bonding agent and the first characteristic enhancing agent.

25. (withdrawn) The method of claim 24 wherein the bonding agent is provided in liquid form and the first characteristic enhancing agent is provided in particulate form, and

wherein the bonding agent and the first characteristic enhancing agent are mixed to provide a colloidal glue such that particles of the first characteristic enhancing agent are dispersed within a substantially continuous medium of the bonding agent.

26. (withdrawn) The method of claim 23 wherein the step of gluing the integrated circuit bearing structure to the substrate structure comprises:

depositing the glue on at least one of the first and second surfaces;  
placing the first and second surfaces in proximity with each other such that the glue extends between the first and second surfaces; and  
curing the glue to bond the integrated circuit bearing structure to the substrate structure.

27. (withdrawn) The method of claim 23 wherein the integrated circuit bearing structure is a wafer, the method comprising:

singulating a plurality of integrated circuits from the wafer, each of the integrated circuits comprising a portion of the wafer, the substrate and the glue.

28. (withdrawn) The method of claim 23 further comprising:

selecting the substrate structure material to have a second characteristic, the second characteristic being another one of the group consisting of thermally conductive, electrically conductive and magnetically permeable.

29. (withdrawn) The method of claim 23 wherein the integrated circuit bearing structure is a first integrated circuit bearing structure, the method further comprising:

providing a second integrated circuit bearing structure;  
connecting the second integrated circuit bearing structure to the first integrated circuit bearing structure.

30. (withdrawn) A method of making a colloidal glue comprising:

selecting a characteristic from the group of thermally conductive, electrically conductive, and magnetically permeable;  
providing a glue having the selected characteristic; and

bonding an integrated circuit layer to a substrate layer using the glue having the selected characteristic.

31. (withdrawn) The method of claim 30 further comprising:  
thinning the integrated circuit layer after bonding.

32. (withdrawn) The method of claim 30 further comprising:  
providing the substrate layer with the selected characteristic.

33. (withdrawn) The method of claim 30 wherein the providing the glue comprises:  
providing a base adhesive agent; and  
adding a characteristic agent to the base adhesive to provide a glue having the selected  
characteristic in colloidal suspension.